



## N-Channel Depletion-Mode Vertical DMOS FETs

### Features

- ▶ High input impedance
- ▶ Low input capacitance
- ▶ Fast switching speeds
- ▶ Low on-resistance
- ▶ Free from secondary breakdown
- ▶ Low input and output leakage

### Applications

- ▶ Normally-on switches
- ▶ Solid state relays
- ▶ Converters
- ▶ Constant current sources
- ▶ Power supply circuits
- ▶ Telecom

### General Description

The Supertex DN3145 is a depletion-mode (normally-on) transistor utilizing an advanced vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

### Ordering Information

Device	Package Option	$BV_{DSX}/BV_{DGX}$ (V)	$R_{DS(ON)}$ (max) ( $\Omega$ )	$I_{DSS}$ (min) (mA)
	TO-243AA (SOT-89)			
DN3145	DN3145N8-G	450	60	120

-G indicates package is RoHS compliant ('Green')



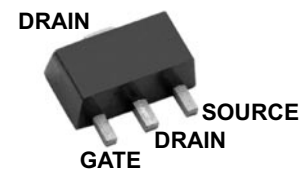
### Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	$BV_{DSX}$
Drain-to-gate voltage	$BV_{DGX}$
Gate-to-source voltage	$\pm 20V$
Operating and storage temperature	$-55^{\circ}C$ to $+150^{\circ}C$
Soldering temperature*	$300^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

\* Distance of 1.6mm from case for 10 seconds.

### Pin Configuration



TO-243AA (SOT-89) (N8)

### Product Marking

**DN1MW** W = Code for week sealed  
 \_\_\_\_\_ = "Green" Packaging

TO-243AA (SOT-89) (N8)

### Thermal Characteristics

Package	$I_D$ (continuous) <sup>†</sup> (mA)	$I_D$ (pulsed) (mA)	Power Dissipation @ $T_A = 25^\circ\text{C}$ (W)	$\theta_{jc}$ ( $^\circ\text{C}/\text{W}$ )	$\theta_{ja}$ ( $^\circ\text{C}/\text{W}$ )	$I_{DR}$ <sup>†</sup> (mA)	$I_{DRM}$ (mA)
TO-243AA	100	300	1.3 <sup>‡</sup>	34	97 <sup>‡</sup>	100	300

**Notes:**

- <sup>†</sup>  $I_D$  (continuous) is limited by max rated  $T_j$ .
- <sup>‡</sup> Mounted on FR4 board, 25mm x 25mm x 1.57mm.

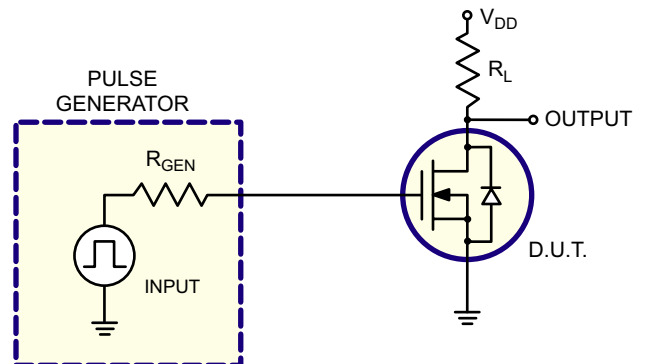
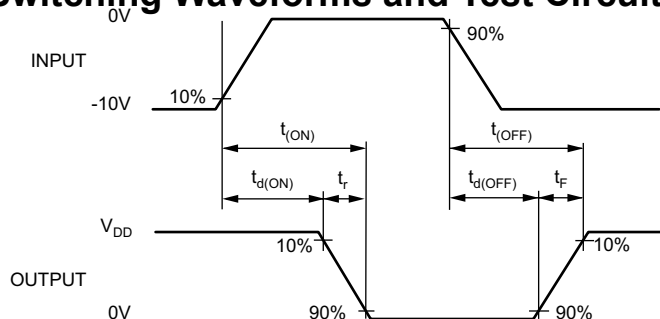
### Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
$BV_{DSX}$	Drain-to-source breakdown voltage	450	-	-	V	$V_{GS} = -5.0\text{V}, I_D = 100\mu\text{A}$
$V_{GS(OFF)}$	Gate-to-source off voltage	-1.5	-	-3.5	V	$V_{DS} = 15\text{V}, I_D = 10\mu\text{A}$
$\Delta V_{GS(OFF)}$	Change in $V_{GS(OFF)}$ with temperature	-	-	-4.5	mV/ $^\circ\text{C}$	$V_{DS} = 15\text{V}, I_D = 10\mu\text{A}$
$I_{GSS}$	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
$I_{D(OFF)}$	Drain-to-source leakage current	-	-	1.0	$\mu\text{A}$	$V_{DS} = \text{Max rating}, V_{GS} = -5.0\text{V}$
		-	-	1.0	mA	$V_{DS} = 0.8 \text{ Max Rating}, V_{GS} = -5.0\text{V}, T_A = 125^\circ\text{C}$
$I_{DSS}$	Saturated drain-to-source current	120	-	-	mA	$V_{GS} = 0\text{V}, V_{DS} = 15\text{V}$
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	-	60	$\Omega$	$V_{GS} = 0\text{V}, I_D = 100\text{mA}$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.1	%/ $^\circ\text{C}$	$V_{GS} = 0\text{V}, I_D = 100\text{mA}$
$G_{FS}$	Forward transconductance	140	-	-	mmho	$V_{DS} = 10\text{V}, I_D = 100\text{mA}$
$C_{ISS}$	Input capacitance	-	-	120	pF	$V_{GS} = -5.0\text{V}, V_{DS} = 25\text{V}, f = 1.0\text{MHz}$
$C_{OSS}$	Common source output capacitance	-	-	15		
$C_{RSS}$	Reverse transfer capacitance	-	-	10		
$t_{d(ON)}$	Turn-on delay time	-	-	10	ns	$V_{DD} = 25\text{V}, I_D = 100\text{mA}, R_{GEN} = 25\Omega,$
$t_r$	Rise time	-	-	15		
$t_{d(OFF)}$	Turn-off delay time	-	-	20		
$t_f$	Fall time	-	-	35		
$V_{SD}$	Diode forward voltage drop	-	-	1.8	V	$V_{GS} = -5.0\text{V}, I_{SD} = 100\text{mA}$
$t_{rr}$	Reverse recovery time	-	800	-	ns	$V_{GS} = -5.0\text{V}, I_{SD} = 100\text{mA}$

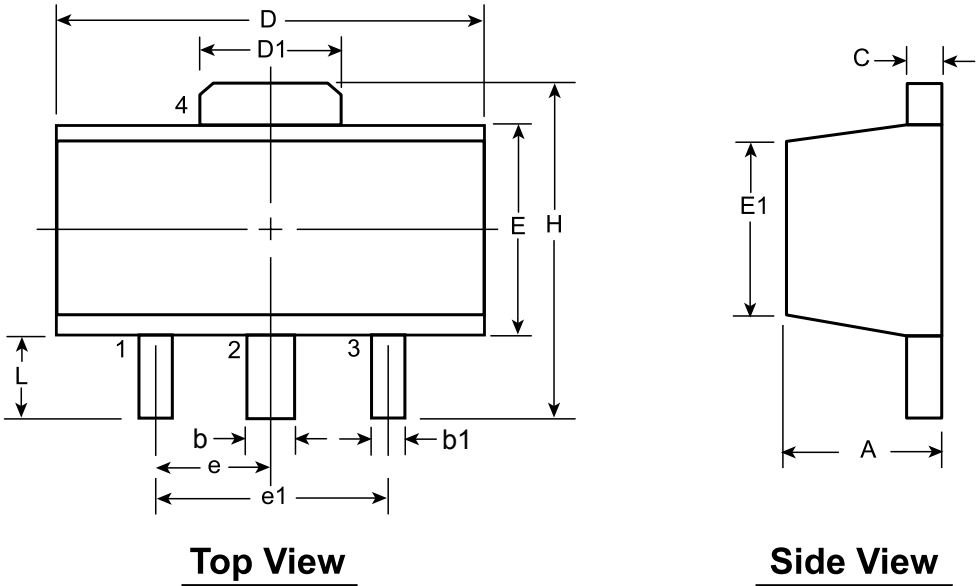
**Notes:**

- All D.C. parameters 100% tested at  $25^\circ\text{C}$  unless otherwise stated. (Pulse test: 300 $\mu\text{s}$  pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

### Switching Waveforms and Test Circuit



### 3-Lead TO-243AA (SOT-89) Package Outline (N8)



**Top View**

**Side View**

Symbol		A	b	b1	C	D	D1	E	E1	e	e1	H	L	
Dimensions (mm)	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.13	1.50 BSC	3.00 BSC	3.94	0.89	
	NOM	-	-	-	-	-	-	-	-			-	-	-
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20	

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.  
 Drawings not to scale.  
 Supertex Doc. #: DSPD-3TO243AAN8, Version D070908.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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